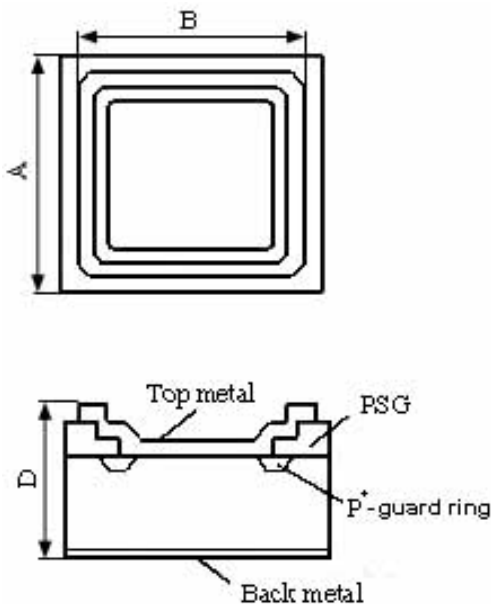


SCHOTTKY DIODE KDN-10030B.
PRELIMINARY



Rev.1. Feb. 2010

	10A/30V. Die Size-115mil.			
Electrical Characteristics	Symbol	Unit	Spec. Limit	Die Sort
Breakdown Voltage @ $I_R=10mA$	V_{BR}	V	30	35
Average Rectified Forward Current	$I_{F(AV)}$	A	10,0	-
DC Forward Voltage @ 25°C, $I_F=10,0A$	V_F	V	0,45	0,43
Maximum Reverse Current @ 25°C, $V_R=35V$ 25°C, $V_R=30V$ 125°C, $V_R=30V$	I_R	mA	- 0,50 300,0	0,80 0,40 250,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	I_{FSM}	A	250	-
Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150^\circ C$.	I_{RRM}	A	5,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	±8 (contact)	
Voltage Rate of Change	dV/dt	V/µS	10.000	
Operating Junction Temperature	T_J	°C	150	



DIM	ITEM	µm
A_x A_y	Wafer Form Die Size	2920 2920
B_x B_y	Top Metal Size	2780 2780
D	Thickness	350max.
Scribe line Width		80

Top metal: a) Ti-Ni-Ag – for Soldering;
b) Al.- for Wire Bonding.
Back metal: Ti-Ni-Ag.